Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2953

Chopper Regulator, DC-DC Converter and Motor Drive Applications

: RDS (ON) = 0.31 Ω (typ.)

• High forward transfer admittance $: |Y_{fs}| = 15 \text{ S (typ.)}$

• Low leakage current $: IDSS = 100 \mu A \text{ (max) (VDS} = 600 \text{ V)}$

• Enhancement-mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

• Low drain-source ON resistance

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	600	V	
Gate-source voltage		V_{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	15	Α	
	Pulse (Note 1)	I _{DP}	60	A 	
Drain power dissipation	n (Tc = 25°C)	P_{D}	90	W	
Single pulse avalanche energy (Note 2)		E _{AS}	1026	mJ	
Avalanche current		I _{AR}	15	Α	
Repetitive avalanche e	nergy (Note 3)	E _{AR}	9	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55~150	°C	

15.8±0.5 03.6±0.2 3.5 15.8±0.5 03.6±0.2 3.5 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60 1.60

Weight: 5.8 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.39	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	41.6	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 7.98 mH, R_G = 25 Ω , I_{AR} = 15 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

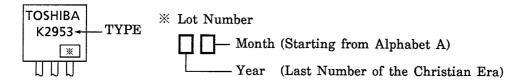
Electrical Characteristics (Ta = 25°C)

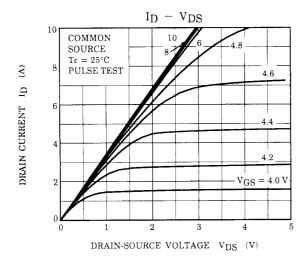
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V _(BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_		V
Drain cut-off cur	rent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V _{(BR)DSS}	I_D = 10 mA, V_{GS} = 0 V	600	_	1	V
Gate threshold v	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source Ol	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 8.0 A	_	0.31	0.4	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 8.0 A	8.0	15.0	_	S
Input capacitano	е	C _{iss}		_	3520	_	
Reverse transfer	capacitance C_{rss} $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		_	20	_	pF	
Output capacitance		C _{oss}]		300		_
Switching time	Rise time	t _r	V_{GS} V_{OV} $I_{D}=8.0A$ $R_{L}=37.5\Omega$ $V_{DD}=300V$	_	50	_	
	Turn-on time	t _{on}		_	100	ı	ns
	Fall time	t _f		_	60	l	TIS
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \mu s$	_	325	-	
Total gate charg plus gate-drain)				80	_		
Gate-source charge		Q_{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		48	_	nC
Gate-drain ("miller") Charge		Q_{gd}			32	_	

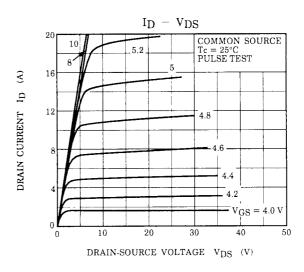
Source-Drain Ratings and Characteristics (Ta = 25°C)

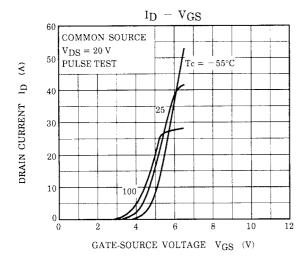
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	-	_	_	15	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	60	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 15 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 15 A, V _{GS} = 0 V dI _{DR} / dt = 100 A / μs		620	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs		7.5	_	μC

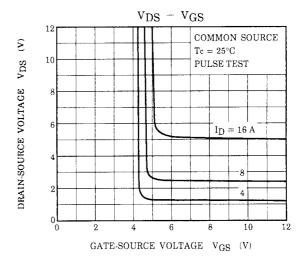
Marking

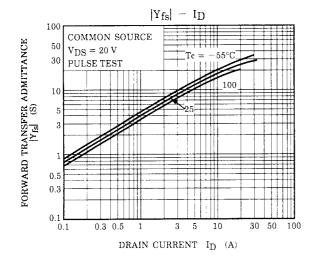


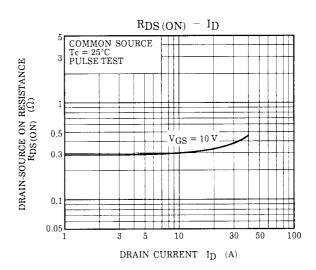




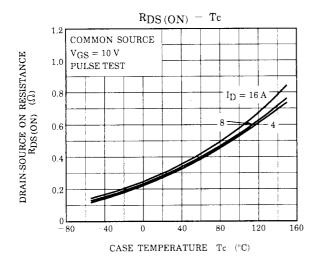


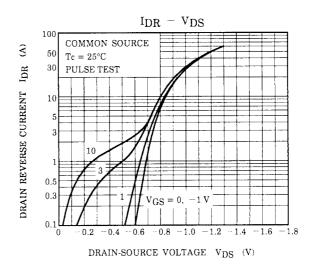


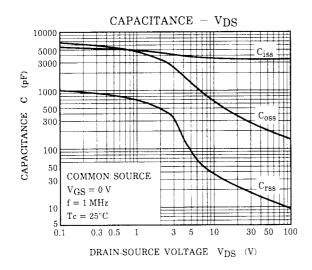


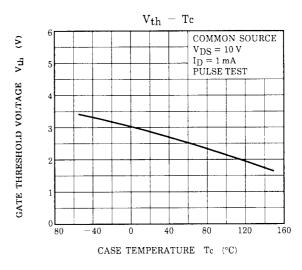


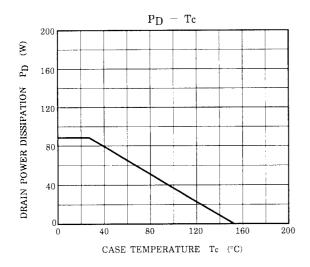
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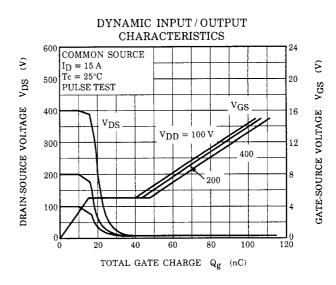




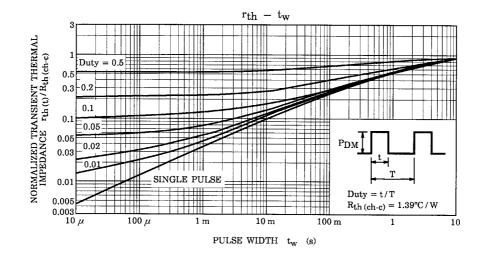


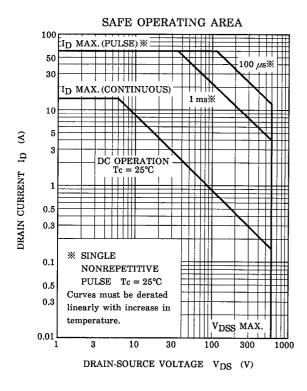


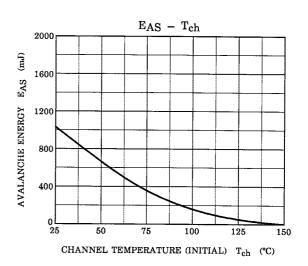


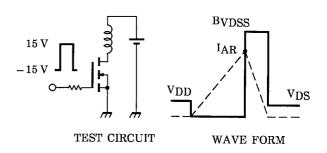


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$$\begin{aligned} R_G &= 25~\Omega \\ V_{DD} &= 90~V,~L = 7.98~mH \end{aligned} \qquad E_{AS} &= \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right) \end{aligned}$$

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